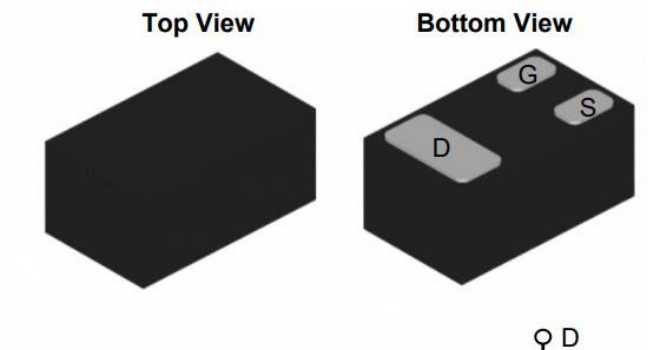
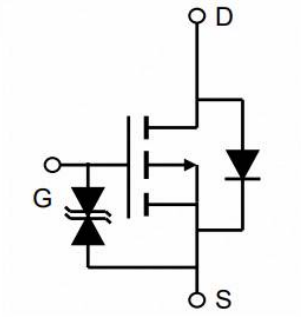
P-Channel Enhancement Mode Field Effect Transistor



DFN1006-3L



Product Summary

- V_{DS} -20V
- I_D -0.65A
- $R_{DS(ON)}$(at V_{GS}=-4.5V) ＜850 mohm
- $R_{DS(ON)}$(at V_{GS}=-2.5V) ＜1200 mohm
- $R_{DS(ON)}$(at V_{GS}=-1.8V) ＜2000 mohm
- ESD Protected Up to 2.0KV (HBM)

General Description

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Interfacing, Logic switch
- Load switch
- Power management

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Maximum	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	±12	V
Drain Current	T_A=25℃ Steady State	I_D	-0.65	A
	T_A=70℃ Steady State		-0.52	
Pulsed Drain Current [A]		I_{DM}	-2.0	A
Total Power Dissipation @ T_A=25℃ Steady State		P_D	0.9	W
Thermal Resistance Junction-to-Ambient @ Steady State [B]		$R_{\theta JA}$	138	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJA3139KA	F1	39	10000	100000	400000	7“ reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=-250μA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V,T_C=25℃			-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±10V, V_{DS}=0V		±1.5	±10	μA
		V_{GS}= ±8V, V_{DS}=0V		±500	±2000	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=-250μA	-0.35	-0.62	-1.2	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= -4.5V, I_D=-0.5A		580	850	mΩ
		V_{GS}= -2.5V, I_D=-0.3A		855	1200	
		V_{GS}= -1.8V, I_D=-0.2A		1350	2000	
Diode Forward Voltage	V_{SD}	I_S=-0.65A,V_{GS}=0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I_S				-0.65	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V,f=1MHZ		71		pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			15		
Gate resistance	Rg	f=1MHz, Open Drain		85		Ω
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=-4.5V,V_{DD}=-10V,I_D=-0.5A		1.24		nC
Gate Source Charge	Q_{gs}			0.37		
Gate Drain Charge	Q_{gd}			0.27		
Reverse Recovery Chrage	Q_{rr}	I_F=-0.5A, di/dt=-20A/us		0.97		
Reverse Recovery Time	t_{rr}			26		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=-4.5V,V_{DD}=-10V, R_L=2.5Ω, R_{GEN}=3Ω		4		
Turn-on Rise Time	t_r			19		
Turn-off Delay Time	$t_{D(off)}$			16		
Turn-off Fall Time	t_f			25		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

B. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_D is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it to.

■ Typical Performance Characteristics

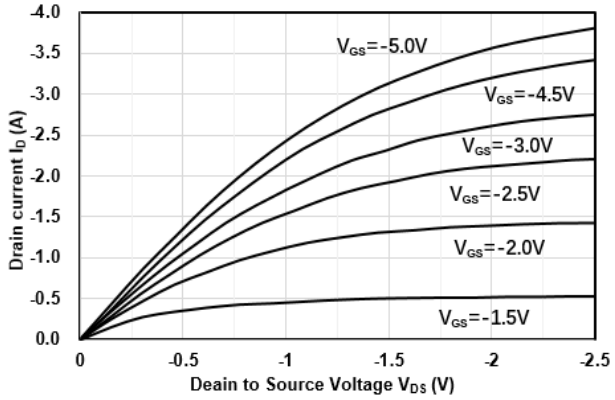


Figure1. Output Characteristics

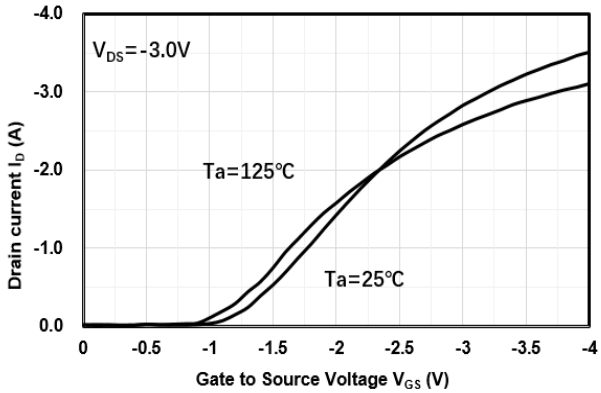


Figure2. Transfer Characteristics

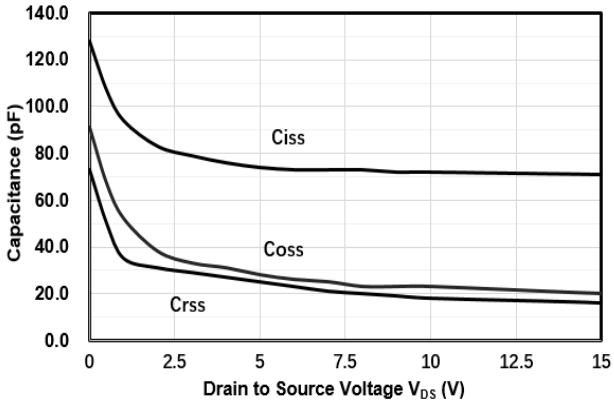


Figure3. Capacitance Characteristics

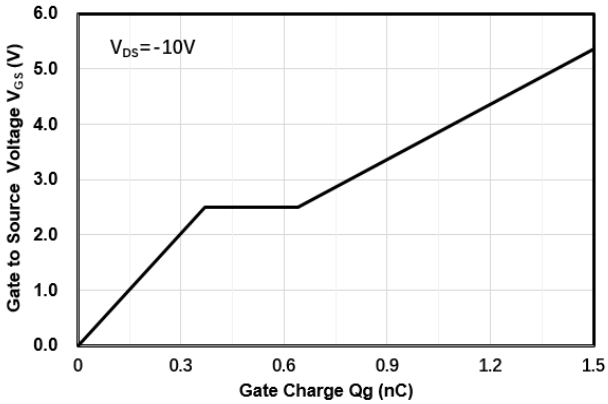


Figure4. Gate Charge

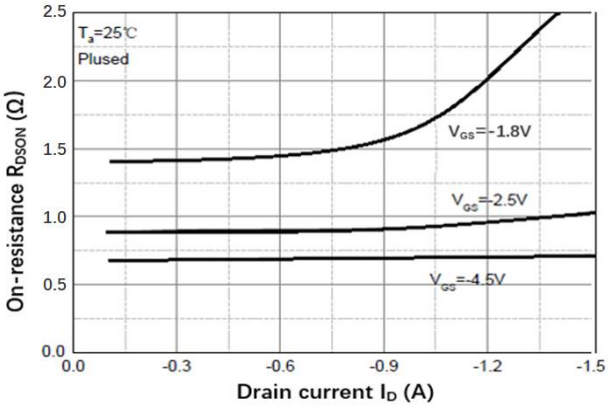


Figure5. Drain-Source on Resistance

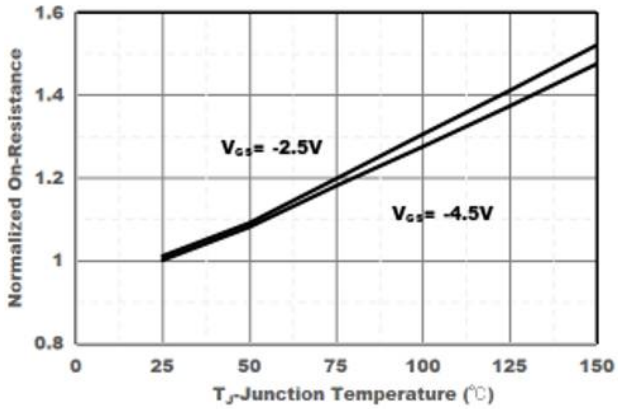


Figure6. Drain-Source on Resistance

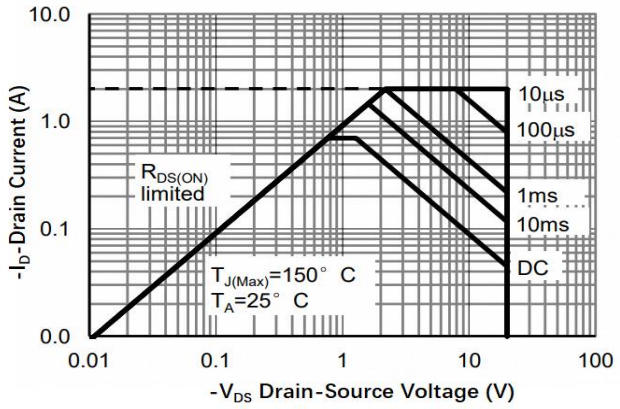


Figure7. Safe Operation Area

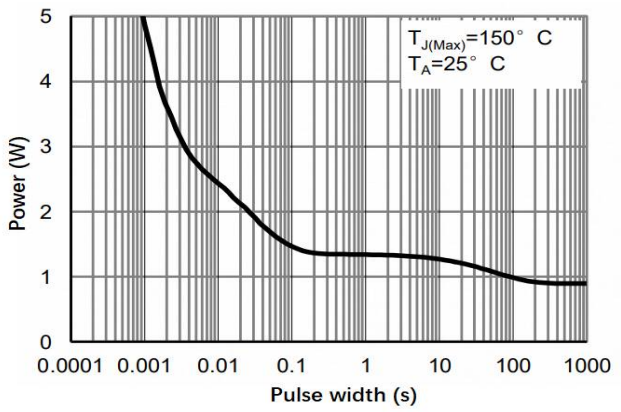


Figure8. Pulse Power Rating Junction-to-Ambient

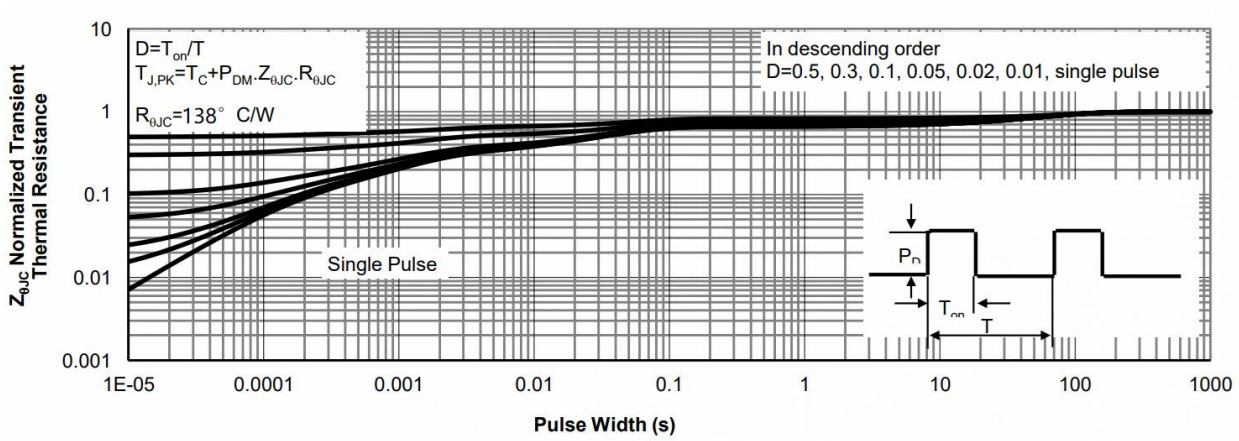
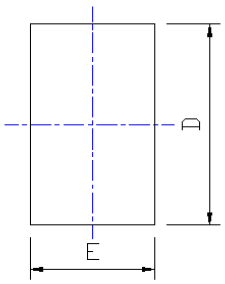
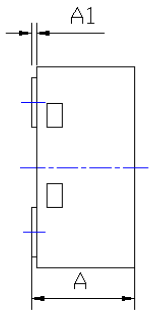


Figure9. Normalized Maximum Transient Thermal Impedance

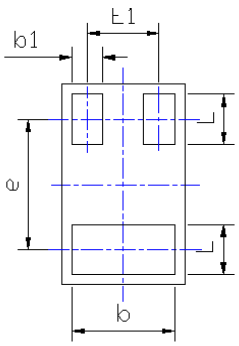
■ DFN1006-3L Package information



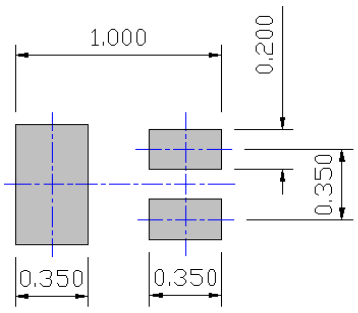
TOP VIEW



SIDE VIEW



BOTTOM VIEW



UNIT：mm

SUGGESTED SOLDER PAD LAYOUT

DIMENSIONS			
SYMBOL	Millimeter		
	MIN.	NOM.	MAX.
A	0.42	---	0.55
A1	0.025REF		
b	0.45	0.50	0.55
b1	0.10	0.15	0.20
D	0.95	1.00	1.05
E	0.55	0.60	0.65
E1	0.35BSC		
e	0.65BSC		
L	0.20	0.25	0.30

NOTE:
1.PACKAGE BODY SIZES EXCLUDE LEAD BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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